

AMENDMENT(S) TO THE SPECIFICATION

Please replace the paragraph beginning at page 4, line 6 to page 4, line 12, with the following rewritten paragraph:

Furthermore, the TFT's used in digital projection LCDs are of polysilicon rather than amorphous silicon. The former have much higher mobility and lower leakage currents than the latter. Polysilicon TFTs are manufactured on quartz substrates so that the devices can be processed at temperatures in excess of ~~1,000~~1,000°C, compared to amorphous silicon devices which are processed on glass sheets with a maximum processing temperature of about ~~600~~600°C. This allows the control circuitry to be located on chip as well as allowing much smaller transistors to be fabricated with acceptable leakage.

Please replace the paragraph beginning at page 6, line 8 to page 7, line 1, with the following rewritten paragraph:

These objects have been achieved by inserting an opaque optical shielding element between the TFT active layer and the lower transparent plate of the LCD. By making the lower transparent plate out of quartz, or similar material, and the shielding element from a refractory material such as tungsten, the TFT active layer can be made of polysilicon (as opposed to amorphous silicon) since the plate and shield element will not be affected by the high temperatures, in excess of ~~1,000~~1,000°C, to which they will be exposed when the polysilicon is processed to form TFTs. Optionally, a glue layer may be inserted between the shield layer and the transparent plate and/or the shield elements may be encapsulated within a barrier layer prior to the deposition of the polysilicon. Another option of the present invention is to omit the conventional black matrix, allowing the shielding elements to take its place.